



2813

Please type a plus sign (+) inside this box → [+]

PTO/SB/21 (08-00)

Approved for use through 10/31/2002. OMB 0651-0031

U.S. Patent and Trademark Office: U.S. DEPARTMENT OF COMMERCE

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it displays a valid OMB control number.

<b>TRANSMITTAL FORM</b> (to be used for all correspondence after initial filing)	Application Number	09/699,466	
	Filing Date	October 31, 2000	
	First Named Inventor	Shunpei YAMAZAKI et al.	
	Group Art Unit	2813	
	Examiner Name	Asok SARKAR	
Total Number of Pages in This Submission		Attorney Docket Number	740756-2222

ENCLOSURES (check all that apply)		
<input type="checkbox"/> Fee Transmittal Form <input type="checkbox"/> Fee Attached <input checked="" type="checkbox"/> Amendment / Reply <input type="checkbox"/> After Final <input type="checkbox"/> Affidavits/declaration(s) <input type="checkbox"/> Extension of Time Request <input type="checkbox"/> Express Abandonment Request <input type="checkbox"/> Information Disclosure Statement <input type="checkbox"/> Certified Copy of Priority Document(s) <input type="checkbox"/> Response to Missing Parts/Incomplete Application <input type="checkbox"/> Response to Missing Parts under 37 CFR 1.52 or 1.53	<input type="checkbox"/> Assignment Papers (for an Application) <input type="checkbox"/> Drawing(s) <input type="checkbox"/> Licensing-related Papers <input type="checkbox"/> Petition <input type="checkbox"/> Petition to Convert to a Provisional Application <input type="checkbox"/> Power of Attorney, Revocation Change of Correspondence Address <input type="checkbox"/> Terminal Disclaimer <input type="checkbox"/> Request for Refund <input type="checkbox"/> CD, Number of CD(s)	<input type="checkbox"/> After Allowance Communication to Group  <b>RECEIVED</b> <b>JUL 10 2001</b> <b>TECHNOLOGY CENTER 2800</b>
Remarks		

SIGNATURE OF APPLICANT, ATTORNEY, OR AGENT	
Firm or Individual name	<u>Luan C. Do</u> Nixon Peabody LLP 8180 Greensboro Drive Suite 800 McLean, VA 22012
Signature	
Date	July 5, 2001

CERTIFICATE OF MAILING		
I hereby certify that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail in an envelope addressed to: Commissioner for Patents, Washington, DC 20231 on this date: <u>7-5-2001</u>		
Type or printed name	<u>SHIRLEY B. STRAIN</u>	
Signature	<u>Shirley B. Strain</u>	Date <u>7-5-01</u>

Burden Hour Statement: This form is estimated to take 0.2 hours to complete. Time will vary depending upon the needs of the individual case. Any comments on the amount of time you are required to complete this form should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, Washington, DC 20231. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, Washington, DC 20231.



#5/hta-ne  
IDS  
PATENT  
740756-002212  
7/12/01

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re PATENT application of:

Shunpei YAMAZAKI et al.

Application No.: 09/699,466

Filed: October 31, 2000

For: METHOD FOR FABRICATING A  
SEMICONDUCTOR DEVICE

)  
)  
)  
) Art Unit: 2813  
) Examiner: Asok SARKAR  
)  
)  
)

RECEIVED  
JUL 10 2001  
TECHNOLOGY CENTER 2800

**REQUEST FOR CORRECTION OF PRIOR  
INFORMATION DISCLOSURE STATEMENT**

Commissioner of Patents  
Washington, D.C. 20231

July 5, 2001

Dear Sir:

Supplemental to the Information Disclosure Statement filed October 31, 2000, attached hereto is corrected page 6 of Form PTO-1449 to be made of record in the above-identified application. Upon further review of the application, the undersigned noticed three typographical errors in the listings of three separate references listed below for which Abstracts had been submitted for each:

1. JP 61-63107 published 4/1/86
2. JP 7-16134 published 6/23/95
3. JP 52-99348 published 11/93

Each corrected reference number has been listed in boldtype on the Form PTO-1449 sheet for the Examiner's convenience. Applicants apologize for the inconvenience caused by these errors.

It is requested that this Request For Corrected Information Disclosure Statement be considered and made of record in the above-captioned application. It is respectfully requested that an Examiner-initialed copy of this form be returned to the undersigned. In particular, the

Application No.: 09/699,466  
Art Unit: 2823

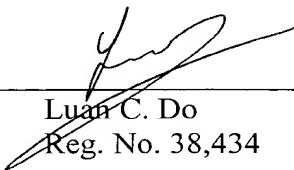
Attorney Docket No.: 740756-2018  
Page 2

Examiner is requested to consider U.S. Patent No. 5,531,182 listed on page 5 of the PTO-1449 form submitted on October 31, 2000.

The Commissioner is hereby authorized to charge any fees connected with this filing which may be required now, or credit any overpayment to Deposit Account No. 19-2380.

Respectfully submitted,

By

  
Luan C. Do  
Reg. No. 38,434

NIXON PEABODY, LLP  
8180 Greensboro Drive, Suite 800  
McLean, Virginia 22102  
Telephone: (703) 770-9110  
Facsimile: (703) 883-0370

EJR/LCD:sbs



09/699,466

61-063017	04/01/86	Japan	Abstract
3-280420 (Japanese & English)	12/11/91	Japan	Full
5-82442	04/02/93	Japan	Abstract
7-161634	06/23/95	Japan	Abstract
2-140915	05/20/90	Japan	Full
1-206632	08/18/89	Japan	Abstract
5-299348	11/93	Japan	Abstract
0178447	09/10/84	European	Full
6-0105216	10/06/85	Japan	Full
1187814	02/27/89	Japan	Full

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

S. Lau et al., "Solid Phase Epitaxy in Silicide Forming System", Thin Solid Films, 47 (1977) pp. 313-322
I.W. Boyd et al., "Oxidation of Silicon Surfaces by CO <sub>2</sub> Lasers", Applied Physics Letters, Vol. 41, No. 2, July 15, 1962, pp. 162-164
S.K. Ghandi, VLSI Fabrication Principles, John Wiley & Sons, 1983, pp. 419-429
P. Zorabedian et al., "Lateral Seeding of Silicon-on-Insu"
T. Hempel et al., "Needle-Like Crystallization of Ni Doped Amorphous Silicon Thin Films", Solid State Communications, Vol. 85, No. 11, pp. 921-924, (1993)
A.V. Dvurechenskii et al., "Transport Phenomena in Amorphous Silicon Doped by Ion Implantation of 3d Metals", Akademikian Lavrentev Prospekt 13, 630090 Novosibirsk 90, USSR, pp. 635-640, Phys. Stat, Sol. (1986)
Kawazu et al., "Low Temperature Crystallization of Hydrogenated Amorphous Silicon Induced by Nickel Silicide Formation", Institute of Applied Physics, Vol. 29, No. 12, pp. 2698-2704, Dec. 1990
Wolf et al., "Silicon Processing for the VLSI Era Vol. 1: Process Technology", Lattice Press 1986, pp. 215-216
R. Kakkad et al., "Crystallized Si Films by Low-Temperature Rapid Thermal Annealing of Amorphous Silicon," J. Appl. Phys., 65(5), March 1, 1989, pp. 2069-72.
G. Liu et al., "Polycrystalline Silicon Thin Film Transistors on Corning 7059 Glass Substrates Using Short Time, Low-Temperature Processing," Appl. Phys. Lett. 62(20), May 17, 1993, pp. 2554-2556.
G. Liu et al. "Selective Area Crystallization of Amorphous Silicon Films by Low-Temperature Rapid Thermal Annealing", Appl. Phys. Lett 55(7), August 14, 1989, pp. 660-662.
R. Kakkad et al., "Low Temperature Selective Crystallization of Amorphous Silicon", Journal of Non-Crystalline Solids, 115, 1989, pp.66-68.
F. Oki et al., Jpn. J. Appl. Phys., 8 (1969) 1056 "Effect of Deposited Metals on the Crystallization Temperature of Amorphous Germanium Film".
T.B. Suresh et al., Thin Solid Films, 252 (1994) 78 "Electroless Plated Ni Contacts to Hydrogenated Amorphous Silicon", 12/94
F. Spaepen et al., Crucial Issued in Semiconductor Materials & Processing Technologies, "Metal-Enhanced Growth in Silicon", (1992) 483-99, 11/92
Wolf et al., "Silicon Processing for the VLSI Era", Vol. 1, pp. 207-211, 1986

DUPLICATE